ESAD25M(C,N,D) (15A) (200V to 400V / 15A)

FAST RECOVERY DIODE

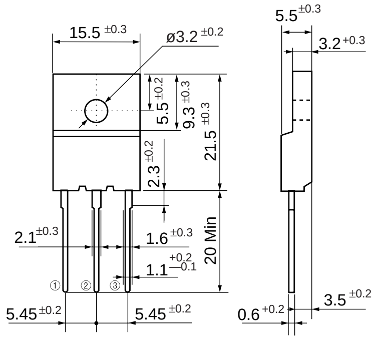
Features

- Insulated package by fully molding
- High voltage by mesa design
- High reliability

Applications

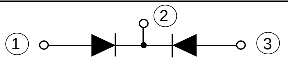
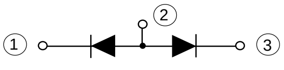
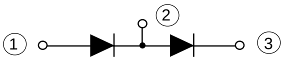
- High speed switching

Outline drawings, mm



JEDEC	——
EIAJ	——

Connection diagram

ESAD25M-□□C	
ESAD25M-□□N	
ESAD25M-□□D	

Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating		Unit
			-02	-04	
Repetitive peak reverse voltage	V_{RRM}		200	400	V
Non-repetitive peak reverse voltage	V_{RSM}		250	450	V
Isolating voltage	Viso	Terminals-to-case, AC.1 min.	1500		V
Average output current	I_O	Square wave, duty=1/2, Tc=98°C	15*		A
Surge current	I_{FSM}	Sine wave 10ms	120		A
Operating junction temperature	T_j		-40 to +150		°C
Storage temperature	T_{stg}		-40 to +150		°C

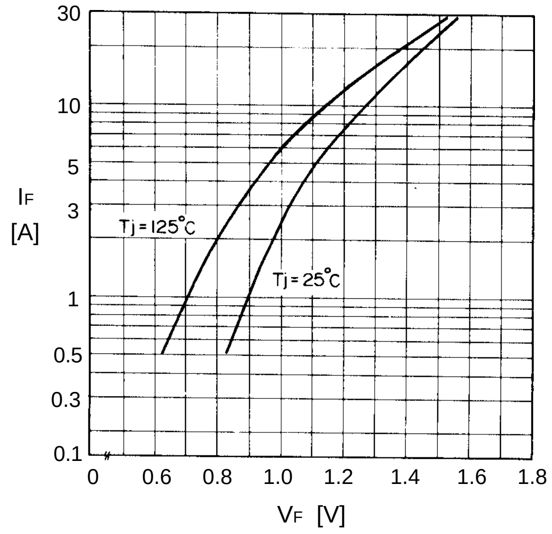
*Average forward current of centertap full wave connection

- Electrical characteristics (Ta=25°C Unless otherwise specified)

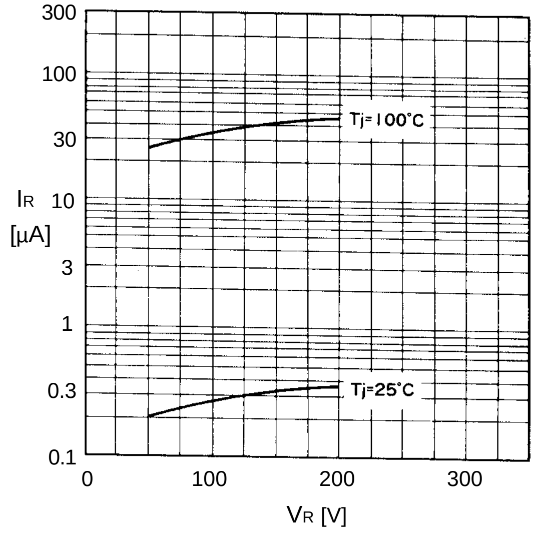
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	I_{FM}=8.0A	1.3	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	0.1	mA
Reverse recovery time	t rr	I_F=0.1A, I_R=0.1A	0.4	µs
Thermal resistance	$R_{th(j-c)}$	Junction to case	2.5*	°C/W

■ Characteristics

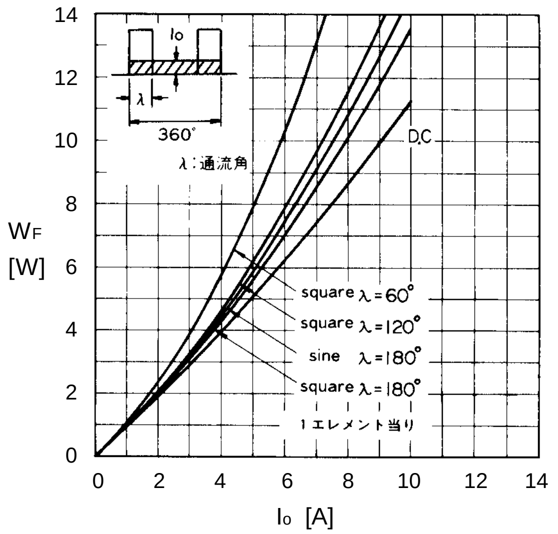
Forward characteristics



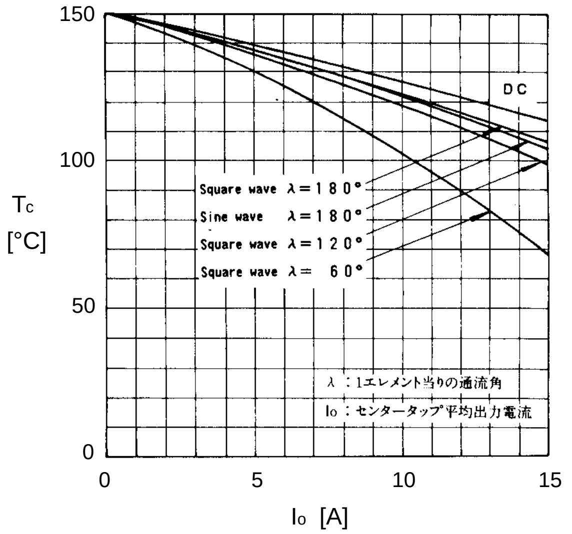
Reverse characteristics



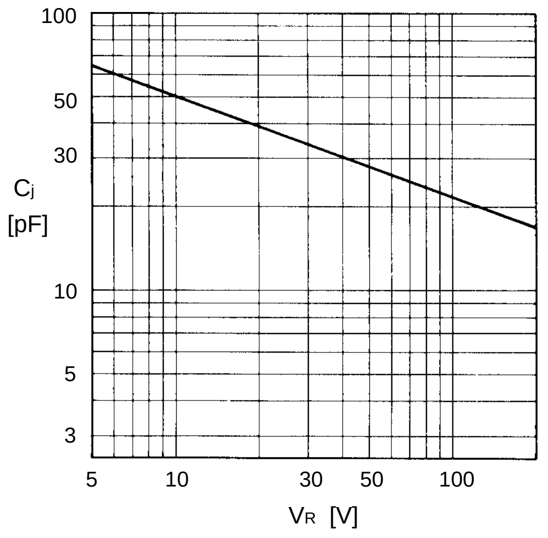
Forward power dissipation



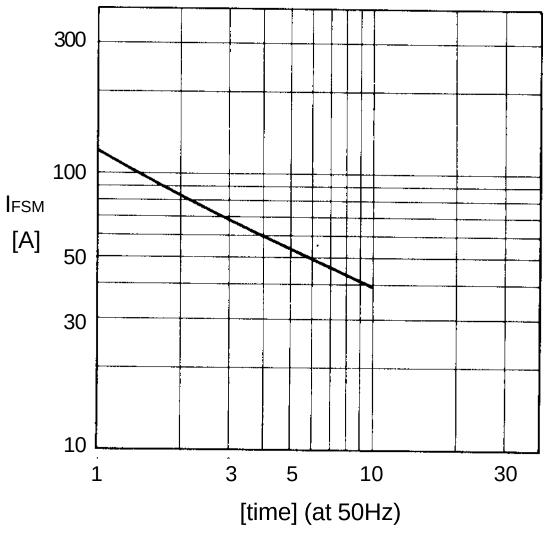
Output current-case temperature



Junction capacitance characteristics



Surge capability



Transient thermal impedance